



Serial No. 09/478,508

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Claim 16 has been amended as follows:

- 1 16. (Amended) A semiconductor device having a semiconductor chip,
- 2 first electrodes formed on said semiconductor chip,
- 3 barrier metals formed on said first electrodes and having laminated structures, and
- 4 a plurality of second protruded electrodes, which serve as external connection terminals,
- 5 formed on said barrier metals, wherein said barrier metals comprising:
 - 6 a lowermost conductive metal layer laminated on said first electrodes, said lowermost
 - 7 conductive metal layer having a joining property with said first electrodes;
 - 8 an intermediate conductive metal layer laminated on said lowermost conductive metal
 - 9 layer, said intermediate conductive metal layer comprising one or more layers and having a joining
 - 10 property with said lowermost conductive metal layer, said intermediate conductive metal layer
 - 11 having at least one layer serving as a barrier layer for preventing said protruded electrodes from
 - 12 diffusing into said intermediate conductive metal layer being made of nickel (Ni); and
 - 13 an uppermost conductive metal layer laminated on said one or more intermediate
 - 14 conductive metal layers, said uppermost conductive metal layer being made of a material which
 - 15 easily alloys with the material of said intermediate conductive metal layers and which has resistance
 - 16 to oxidation, wherein said uppermost conductive metal layer is being made of a metal selected from

17 the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or
18 of an alloy containing a metal selected from the group consisting of gold (Au), platinum (Pt),
19 palladium (Pd), silver (Ag) and rhodium (Rh).